

Milton Feng

List of Publications by Year in descending order

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47
papers

489
citations

933447

10
h-index

794594

19
g-index

47
all docs

47
docs citations

47
times ranked

374
citing authors

#	ARTICLE	IF	CITATIONS
1	Superconducting Processor Modulated VCSELs for 4K High-Speed Optical Data Link. IEEE Journal of Quantum Electronics, 2022, 58, 1-8.	1.9	4
2	Single-mode 850nm VCSELs Demonstrate 96 Gb/s PAM4 OM4 Fiber Link for Extended Reach to 1km. , 2022, , ,		1
3	2.9â€‰%K VCSEL demonstrates 100 Gbps PAM-4 optical data transmission. Applied Physics Letters, 2022, 121, .	3.3	2
4	2.6â€‰%K VCSEL data link for cryogenic computing. Applied Physics Letters, 2021, 119, .	3.3	8
5	Cryogenic Oxide-VCSEL for PAM-4 Optical Data Transmission Over 50 Gb/s at 77 K. IEEE Photonics Technology Letters, 2021, 33, 816-819.	2.5	5
6	Cryogenic Oxide-VCSELs with Bandwidth over 50 GHz at 82 K for Next-Gen High-Speed Computing. , 2021, , ,		3
7	Advanced Single-Mode 850 nm VCSELs for Record NRZ and PAM4 Data Rate on SMF-28 Fiber up to 1 km. , 2021, , .		2
8	Comparison of High-Speed PAM4 and QAM-OFDM Data Transmission Using Single-Mode VCSEL in OM5 and OM4 MMF Links. IEEE Journal of Selected Topics in Quantum Electronics, 2020, 26, 1-10.	2.9	19
9	Comparison on OM5-MMF and OM4-MMF Data Links With 32-GBaud PAM-4 Modulated Few-Mode VCSEL at 850Ånm. Journal of Lightwave Technology, 2020, 38, 573-582.	4.6	7
10	850-nm Single-Mode Vertical-Cavity Surface-Emitting Lasers for 40 Gb/s Error-Free Transmission up to 500 m in OM4 Fiber. IEEE Electron Device Letters, 2020, 41, 84-86.	3.9	7
11	Temperature and Noise Dependence of Tri-Mode VCSEL Carried 120-Gbit/s QAM-OFDM Data in Back-to-Back and OM5-MMF Links. Journal of Lightwave Technology, 2020, 38, 6746-6758.	4.6	11
12	The Modal Effect of VCSELs on Transmitting Data Rate Over Distance in OM4 Fiber. IEEE Journal of Quantum Electronics, 2020, 56, 1-6.	1.9	10
13	Process Optimization and Microwave Model of GaAs Photodiodes for 50 Gb/s Optical Links. IEEE Transactions on Semiconductor Manufacturing, 2020, 33, 557-563.	1.7	0
14	Cryogenic 50 GHz VCSEL for sub-100 fJ/bit Optical Link. , 2020, , .		3
15	Baldur: A Power-Efficient and Scalable Network Using All-Optical Switches. , 2020, , .		3
16	Integrated Photonics of Transistor Laser, Detector and Active Load for All Optical NOR Gate. , 2019, , .		0
17	A NRZ-OOK Modulated 850-nm VCSEL with 54 Gb/s Error-Free Data Transmission. , 2019, , .		4
18	VCSEL with bi-layer oxidized aperture enables 140-Gbit/s OFDM Transmission over 100-m-long OM5 MMF. , 2019, , .		7

#	ARTICLE	IF	CITATIONS
19	850 nm VCSELs for 50 Gb/s NRZ Error-Free Transmission over 100-meter OM4 and up to 115 Å°C Operation. , 2019, , .		7
20	85Å°C Operation of Single-Mode 850 nm VCSELs for High Speed Error-Free Transmission up to 1 km in OM4 Fiber. , 2019, , .		7
21	Tunneling Modulation of Transistor Lasers: Theory and Experiment. IEEE Journal of Quantum Electronics, 2018, 54, 1-14.	1.9	12
22	Oxide-Confined VCSELs for High-Speed Optical Interconnects. IEEE Journal of Quantum Electronics, 2018, 54, 1-15.	1.9	38
23	50 Gb/s Error-Free Data Transmission Using a NRZ-OOK Modulated 850 nm VCSEL. , 2018, , .		5
24	Direct and photon-assisted tunneling in resonant-cavity quantum-well light-emitting transistors. Journal of Applied Physics, 2018, 124, .	2.5	1
25	All optical NOR gate via tunnel-junction transistor lasers for high speed optical logic processors. , 2018, , .		3
26	85Å°C Operation of 850 nm VCSELs Deliver a 42 Gb/s Error-Free Data Transmission for 100 meter MMF Link. , 2018, , .		5
27	High-Speed Visible Light Communication Using GaN-Based Light-emitting Diodes With Photonic Crystals. Journal of Lightwave Technology, 2017, 35, 258-264.	4.6	26
28	Temperature Dependent Analysis of 50 Gb/s Oxide-Confined VCSELs. , 2017, , .		6
29	850 nm Oxide-Confined VCSELs with 50 Gb/s Error-Free Transmission Operating up to 85 Å°C. , 2016, , .		16
30	50 Gb/s Error-Free Data Transmission of 850 nm Oxide-Confined VCSELs. , 2016, , .		15
31	Single Quantum-Well Transistor Lasers Operating Error-Free at 22 Gb/s. IEEE Photonics Technology Letters, 2015, 27, 600-603.	2.5	7
32	Effect of microcavity size to the RIN and 40 Gb/s data transmission performance of high speed VCSELs. , 2015, , .		4
33	0.5 THz Performance of a Type-II DHBT With a Doping-Graded and Constant-Composition GaAsSb Base. IEEE Electron Device Letters, 2014, 35, 24-26.	3.9	7
34	Advanced Process and Modeling on 600+ GHz Emitter Ledge Type-II GaAsSb/InP DHBT. , 2014, , .		1
35	850 nm Oxide-VCSEL With Low Relative Intensity Noise and 40 Gb/s Error Free Data Transmission. IEEE Photonics Technology Letters, 2014, 26, 289-292.	2.5	45
36	Low Power Operation of a Vertical Cavity Transistor Laser via the Reduction of Collector Offset Voltage. IEEE Photonics Technology Letters, 2014, 26, 1003-1006.	2.5	6

#	ARTICLE	IF	CITATIONS
37	Transistor Laser With 13.5-Gb/s Error-Free Data Transmission. IEEE Photonics Technology Letters, 2014, 26, 1542-1545.	2.5	6
38	780 nm Oxide-Confined VCSEL With 13.5 Gb/s Error-Free Data Transmission. IEEE Photonics Technology Letters, 2014, 26, 702-705.	2.5	3
39	50th Anniversary of the Light-Emitting Diode (LED): An Ultimate Lamp [Scanning the Issue]. Proceedings of the IEEE, 2013, 101, 2154-2157.	21.3	13
40	InP/InAlGaAs light-emitting transistors and transistor lasers with a carbon-doped base layer. Journal of Applied Physics, 2011, 109, 063106.	2.5	15
41	InAlGaAs $\hat{\cdot}$ InP light-emitting transistors operating near 1.55 $\hat{1}$ / ₄ m. Journal of Applied Physics, 2008, 103, 114505.	2.5	13
42	High performance GaAsSb $\hat{\cdot}$ InP double heterojunction bipolar transistors grown by gas-source molecular beam epitaxy. Journal of Vacuum Science & Technology B, 2006, 24, 1564.	1.3	3
43	12.5 nm base pseudomorphic heterojunction bipolar transistors achieving $f_T=710$ GHz and $f_{MAX}=340$ GHz. Applied Physics Letters, 2005, 87, 252109.	3.3	59
44	Experimental demonstration of pseudomorphic heterojunction bipolar transistors with cutoff frequencies above 600GHz. Applied Physics Letters, 2005, 86, 152101.	3.3	60
45	Development of Broadband Low Actuation Voltage RF MEM Switches. Active and Passive Electronic Components, 2002, 25, 97-111.	0.3	2
46	Efficient electromagnetic analysis of two-dimensional finite quasi-random gratings for quantum well infrared photodetectors. Journal of Applied Physics, 1998, 83, 3360-3363.	2.5	6
47	Microwave surface resistance of spin $\hat{\epsilon}$ cast YBa ₂ Cu ₃ O ₇ $\hat{\sim}$ x thin films on LaAlO ₃ substrates. Applied Physics Letters, 1993, 63, 3512-3514.	3.3	2